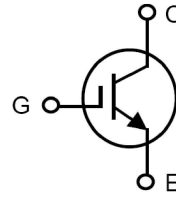


**1200V XPT™
GenX4™ IGBT**

**IXYA20N120C4HV
IXYP20N120C4**

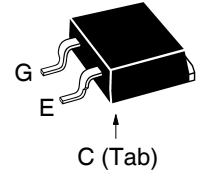
V_{CES} = 1200V
I_{C110} = 20A
V_{CE(sat)} ≤ 2.5V
t_{fi(typ)} = 58ns

High-Speed IGBT
for 20-50 kHz Switching

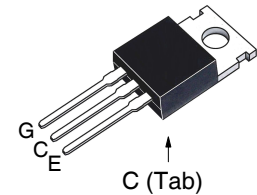


| Symbol | Test Conditions | Maximum Ratings | |
|-------------------------|--|--|----------|
| V _{CES} | T _J = 25°C to 175°C | 1200 | V |
| V _{CGR} | T _J = 25°C to 175°C, R _{GE} = 1MΩ | 1200 | V |
| V _{GES} | Continuous | ±20 | V |
| V _{GEM} | Transient | ±30 | V |
| I _{C25} | T _C = 25°C | 68 | A |
| I _{C110} | T _C = 110°C | 20 | A |
| I _{CM} | T _C = 25°C, 1ms | 120 | A |
| SSOA (RBSOA) | V _{GE} = 15V, T _{VJ} = 150°C, R _G = 10Ω Clamped Inductive Load | I _{CM} = 40 V _{CE} ≤ 0.8 • V _{CES} | A |
| P _C | T _C = 25°C | 375 | W |
| T _J | | -55 ... +175 | °C |
| T _{JM} | | 175 | °C |
| T _{stg} | | -55 ... +175 | °C |
| T _L | Maximum Lead Temperature for Soldering | 300 | °C |
| T _{SOLD} | 1.6 mm (0.062in.) from Case for 10s | 260 | °C |
| M _d | Mounting Torque (TO-220) | 1.13/10 | Nm/lb.in |
| F _C | Mounting Force (TO-263HV) | 10..65 / 22..14.6 | N/lb |
| Weight | TO-263HV | 2.5 | g |
| | TO-220 | 3.0 | g |

**TO-263HV
(IXYA..HV)**



**TO-220
(IXYP)**



G = Gate D = Collector
E = Emitter Tab = Collector

Features

- Optimized for 20-50kHz Switching
- Positive Thermal Coefficient of V_{ce(sat)}
- International Standard Packages

Advantages

- High Power Density
- Low Gate Drive Requirement

Applications

- Power Inverters
- UPS
- Motor Drives
- SMPS
- Battery Chargers
- Welding Machines
- Lamp Ballasts

| Symbol | Test Conditions (T _J = 25°C, Unless Otherwise Specified) | Characteristic Values | | |
|----------------------------|---|-----------------------|------------|---------------|
| | | Min. | Typ. | Max. |
| BV_{CES} | I _C = 250μA, V _{GE} = 0V | 1200 | | V |
| V_{GE(th)} | I _C = 250μA, V _{CE} = V _{GE} | 4.0 | | 6.5 V |
| I_{CES} | V _{CE} = V _{CES} , V _{GE} = 0V T _J = 150°C | | | 25 μA 5 mA |
| I_{GES} | V _{CE} = 0V, V _{GE} = ±20V | | | ±100 nA |
| V_{CE(sat)} | I _C = 20A, V _{GE} = 15V, Note 1 T _J = 150°C | | 2.1 2.5 | V V |

| Symbol Test Conditions ($T_J = 25^\circ\text{C}$ Unless Otherwise Specified) | | Characteristic Values | | |
|--|--|-----------------------|------|-------------------------|
| | | Min. | Typ. | Max. |
| g_{fs} | $I_C = 20\text{A}, V_{CE} = 10\text{V}$, Note 1 | 7.5 | 12.5 | S |
| C_{ies} | $V_{CE} = 25\text{V}, V_{GE} = 0\text{V}, f = 1\text{MHz}$ | | 890 | pF |
| C_{oes} | | | 95 | pF |
| C_{res} | | | 33 | pF |
| $Q_{g(on)}$ | $I_C = 20\text{A}, V_{GE} = 15\text{V}, V_{CE} = 0.5 \cdot V_{CES}$ | | 44 | nC |
| Q_{ge} | | | 8 | nC |
| Q_{gc} | | | 20 | nC |
| $t_{d(on)}$ | Inductive load, $T_J = 25^\circ\text{C}$ $I_C = 20\text{A}, V_{GE} = 15\text{V}$ $V_{CE} = 0.8 \cdot V_{CES}, R_G = 10\Omega$ Note 2 | | 14 | ns |
| t_{ri} | | | 53 | ns |
| E_{on} | | | 4.4 | mJ |
| $t_{d(off)}$ | | | 160 | ns |
| t_{fi} | | | 58 | ns |
| E_{off} | | | 1.0 | mJ |
| $t_{d(on)}$ | Inductive load, $T_J = 125^\circ\text{C}$ $I_C = 20\text{A}, V_{GE} = 15\text{V}$ $V_{CE} = 0.8 \cdot V_{CES}, R_G = 10\Omega$ Note 2 | | 13 | ns |
| t_{ri} | | | 37 | ns |
| E_{on} | | | 4.9 | mJ |
| $t_{d(off)}$ | | | 200 | ns |
| t_{fi} | | | 86 | ns |
| E_{off} | | | 1.6 | mJ |
| R_{thJC} | TO-220 | | | 0.40 $^\circ\text{C/W}$ |
| R_{thCS} | | 0.50 | | $^\circ\text{C/W}$ |

Notes:

1. Pulse test, $t \leq 300\mu\text{s}$, duty cycle, $d \leq 2\%$.
2. Switching times & energy losses may increase for higher V_{CE} (clamp), T_J or R_G .

IXYS Reserves the Right to Change Limits, Test Conditions, and Dimensions.

| | | | | | | | | | | |
|---|-----------|-----------|-----------|-----------|--------------|--------------|--------------|--------------|--------------|-------------|
| IXYS MOSFETs and IGBTs are covered | 4,835,592 | 4,931,844 | 5,049,961 | 5,237,481 | 6,162,665 | 6,404,065 B1 | 6,683,344 | 6,727,585 | 7,005,734 B2 | 7,157,338B2 |
| by one or more of the following U.S. patents: | 4,860,072 | 5,017,508 | 5,063,307 | 5,381,025 | 6,259,123 B1 | 6,534,343 | 6,710,405 B2 | 6,759,692 | 7,063,975 B2 | |
| | 4,881,106 | 5,034,796 | 5,187,117 | 5,486,715 | 6,306,728 B1 | 6,583,505 | 6,710,463 | 6,771,478 B2 | 7,071,537 | |

Fig. 1. Output Characteristics @ $T_J = 25^\circ\text{C}$

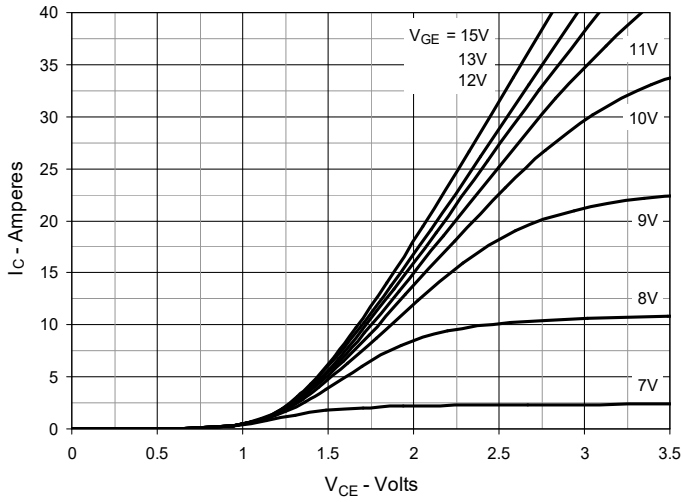


Fig. 2. Extended Output Characteristics @ $T_J = 25^\circ\text{C}$

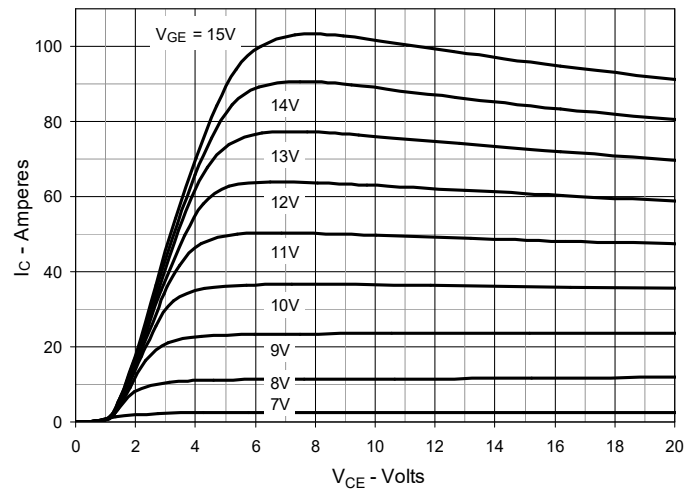


Fig. 3. Output Characteristics @ $T_J = 150^\circ\text{C}$

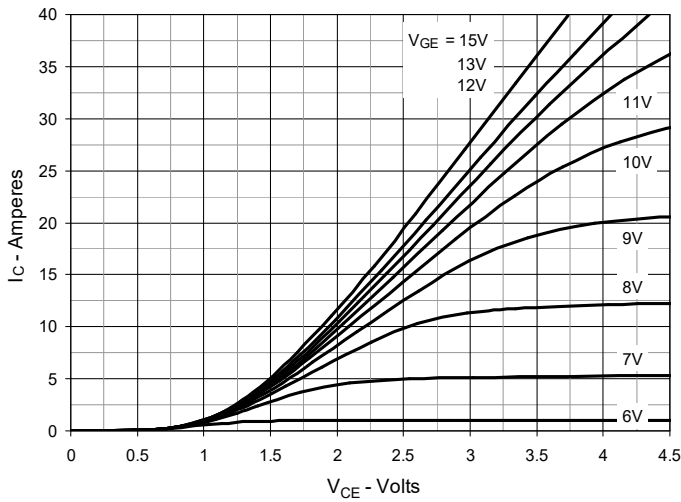


Fig. 4. Dependence of $V_{CE(sat)}$ on Junction Temperature

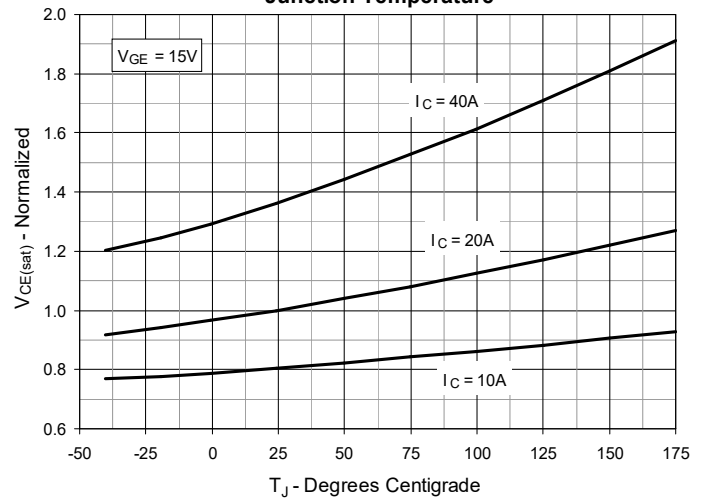


Fig. 5. Collector-to-Emitter Voltage vs. Gate-to-Emitter Voltage

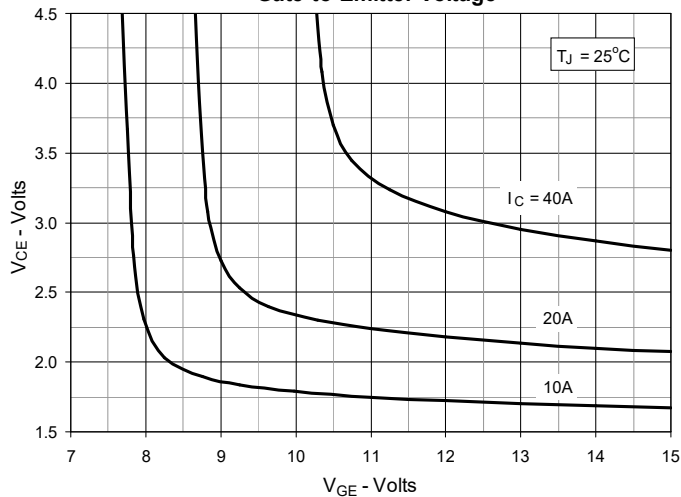


Fig. 6. Input Admittance

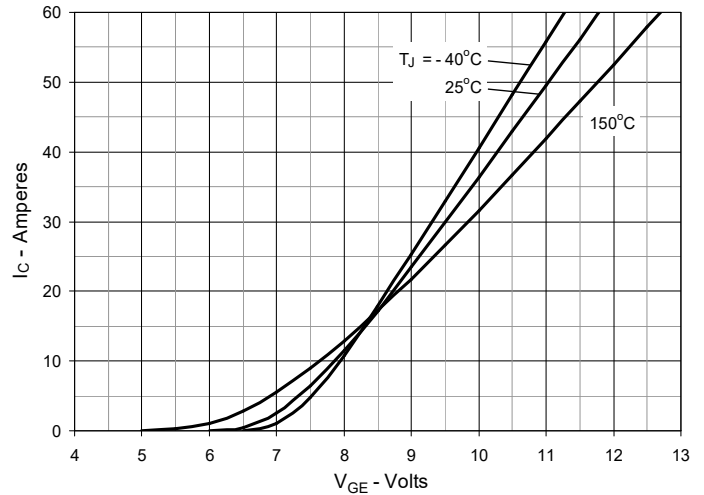


Fig. 7. Transconductance

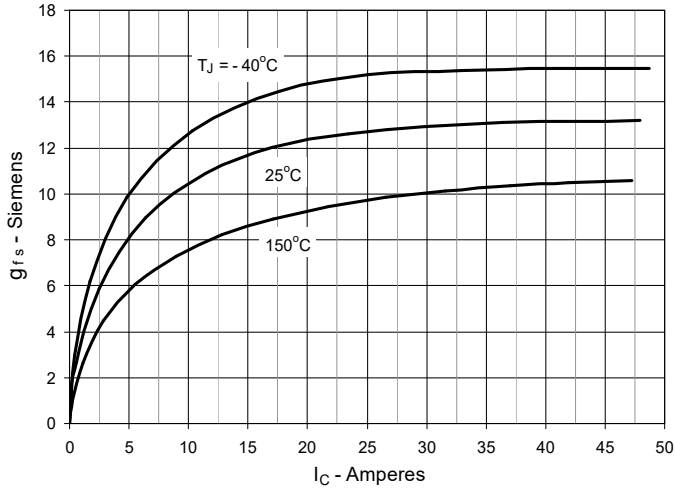


Fig. 8. Gate Charge

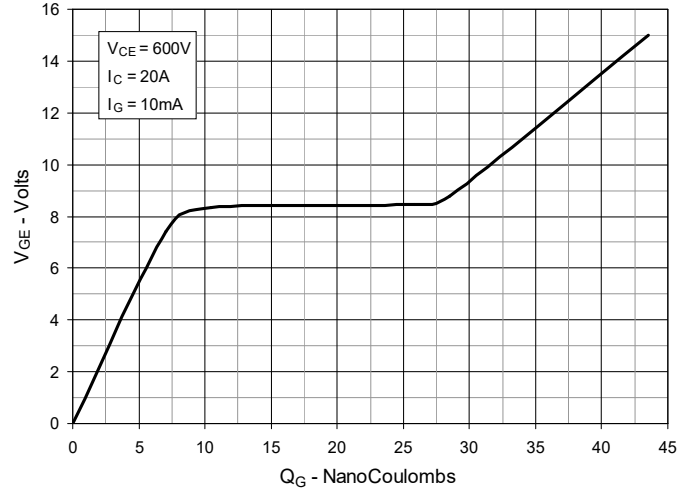


Fig. 9. Capacitance

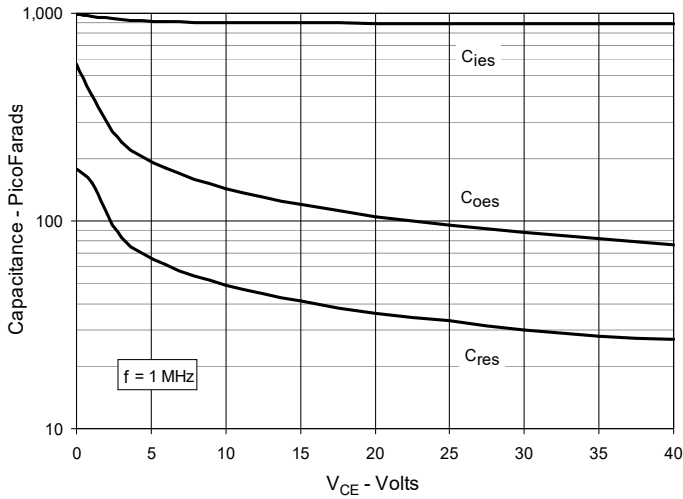


Fig. 10. Reverse-Bias Safe Operating Area

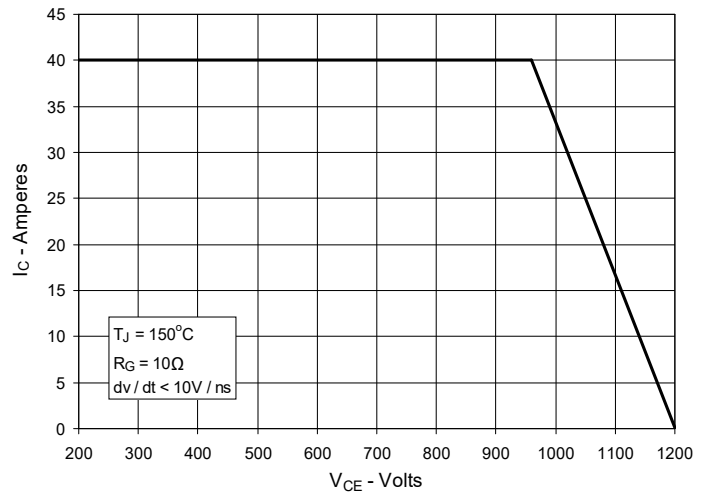


Fig. 11. Maximum Transient Thermal Impedance

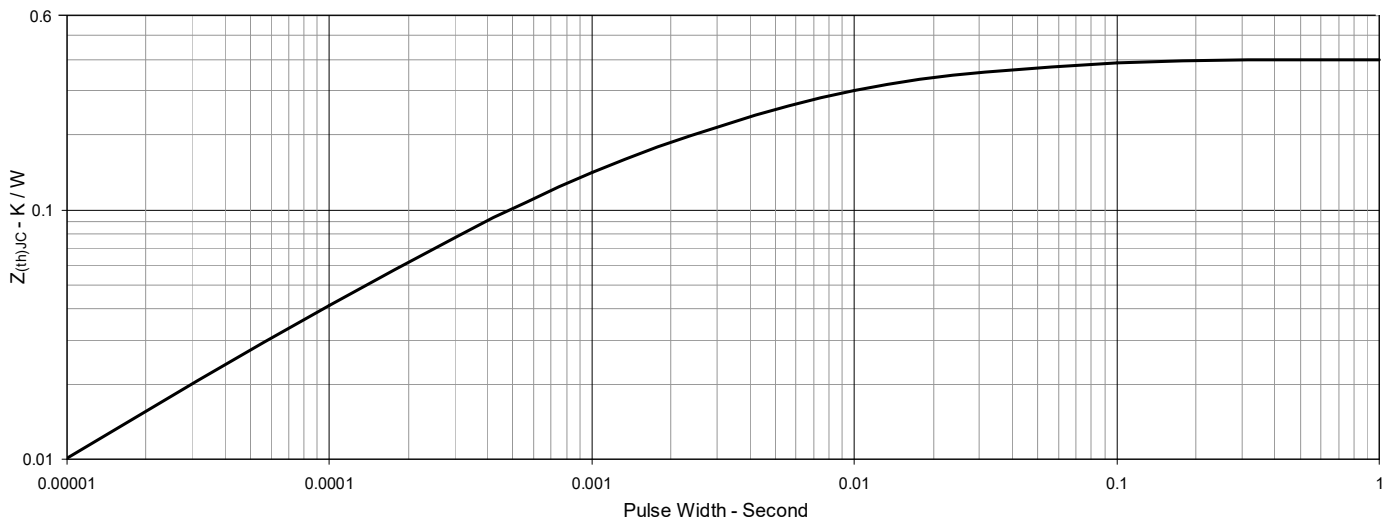


Fig. 12. Inductive Switching Energy Loss vs. Gate Resistance

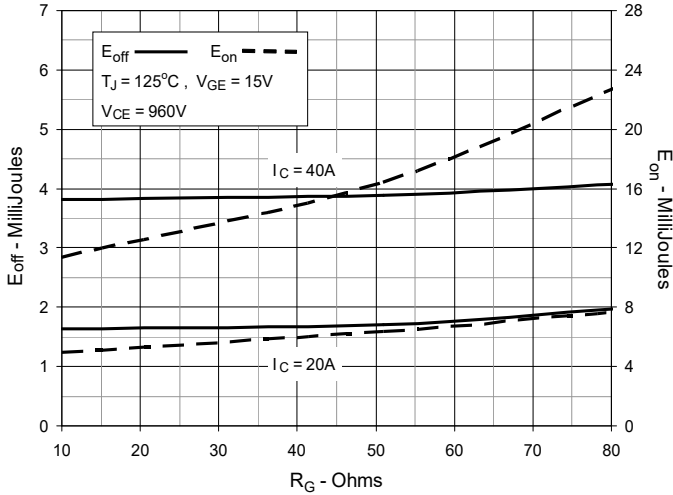


Fig. 13. Inductive Switching Energy Loss vs. Collector Current

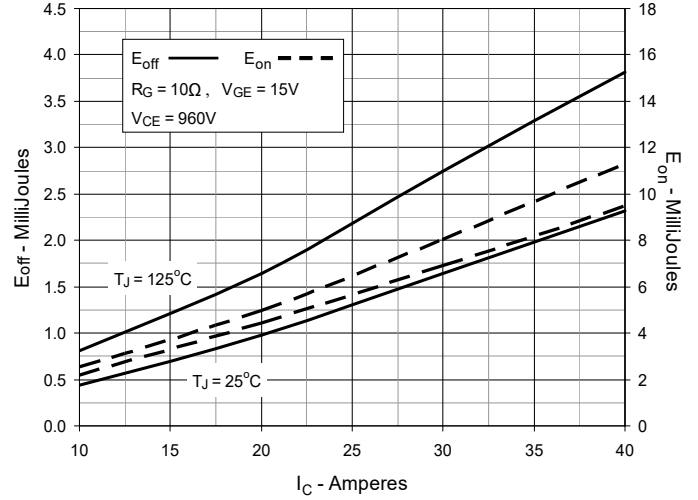


Fig. 14. Inductive Switching Energy Loss vs. Junction Temperature

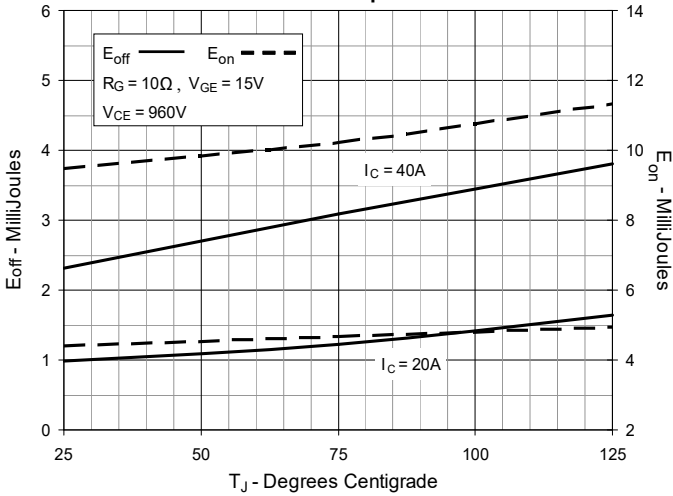


Fig. 15. Inductive Turn-off Switching Times vs. Gate Resistance

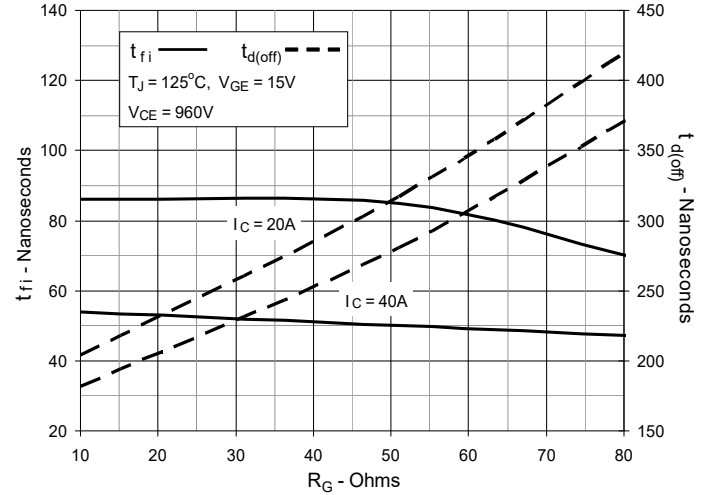


Fig. 16. Inductive Turn-off Switching Times vs. Collector Current

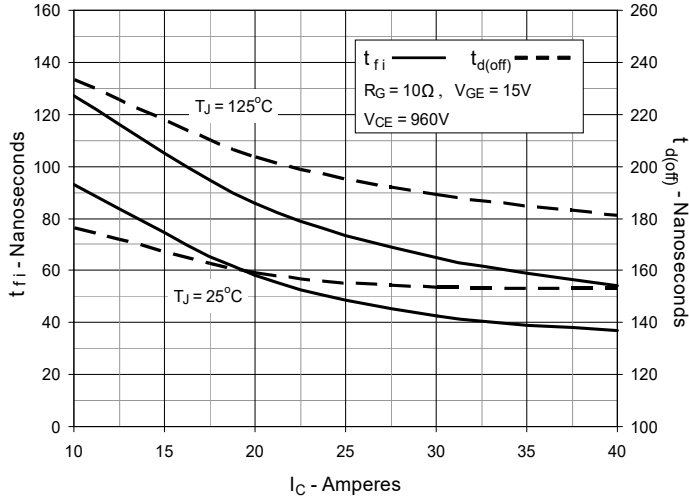


Fig. 17. Inductive Turn-off Switching Times vs. Junction Temperature

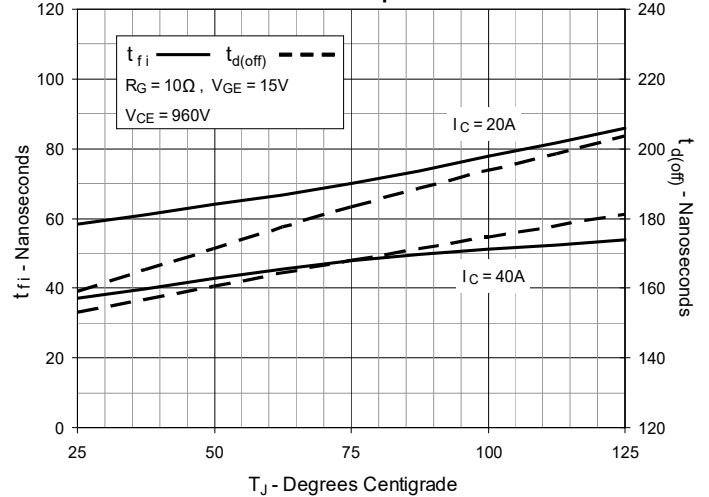


Fig. 18. Inductive Turn-on Switching Times vs. Gate Resistance

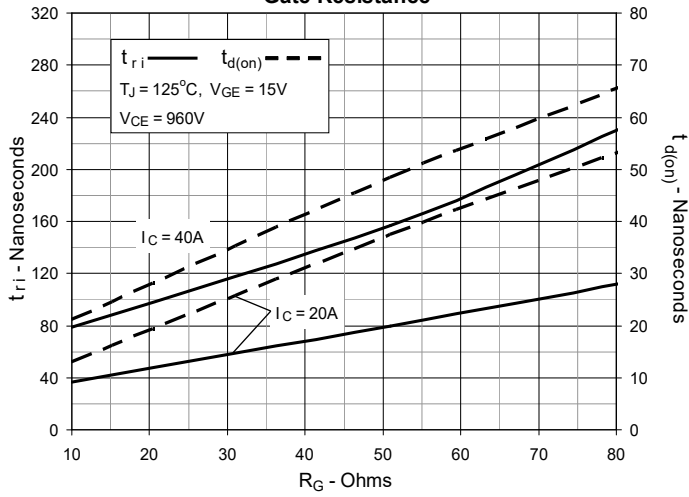


Fig. 19. Inductive Turn-on Switching Times vs. Collector Current

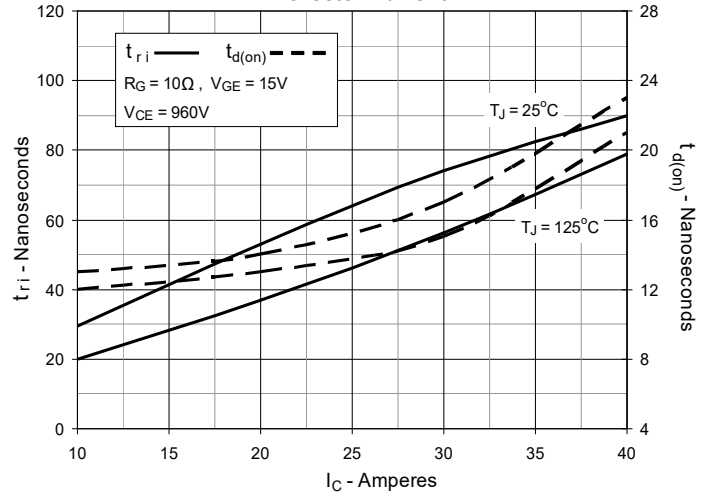
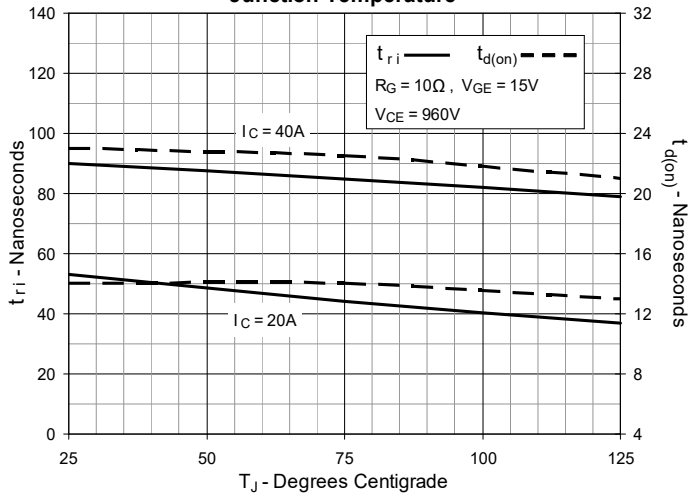
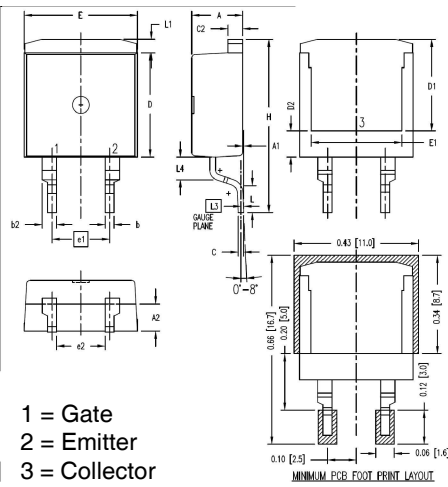


Fig. 20. Inductive Turn-on Switching Times vs. Junction Temperature

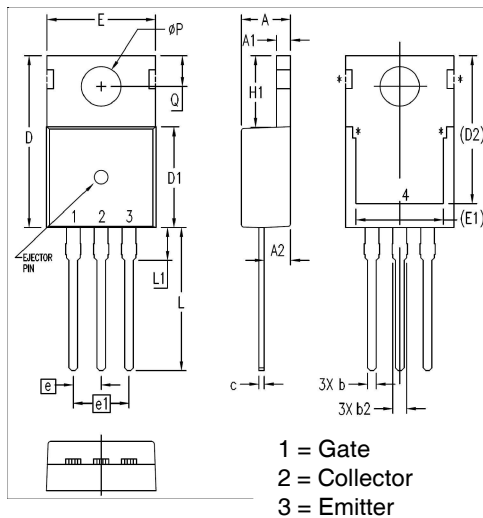


TO-263HV Outline



| SYM | INCHES | | MILLIMETER | |
|------|----------|------|------------|-------|
| | MIN | MAX | MIN | MAX |
| A | .170 | .185 | 4.30 | 4.70 |
| A1 | .000 | .008 | 0.00 | 0.20 |
| A2 | .091 | .098 | 2.30 | 2.50 |
| b | .028 | .035 | 0.70 | 0.90 |
| b2 | .046 | .054 | 1.18 | 1.38 |
| C | .018 | .024 | 0.45 | 0.60 |
| C2 | .049 | .055 | 1.25 | 1.40 |
| D | .354 | .370 | 9.00 | 9.40 |
| D1 | .311 | .327 | 7.90 | 8.30 |
| D2 | .083 | .098 | 2.10 | 2.50 |
| E | .386 | .402 | 9.80 | 10.20 |
| E1 | .307 | .323 | 7.80 | 8.20 |
| e1 | .200 BSC | | 5.08 BSC | |
| (e2) | .163 | .174 | 4.13 | 4.43 |
| H | .591 | .614 | 15.00 | 15.60 |
| L | .079 | .102 | 2.00 | 2.60 |
| L1 | .039 | .055 | 1.00 | 1.40 |
| L3 | .010 BSC | | 0.254 BSC | |
| (L4) | .071 | .087 | 1.80 | 2.20 |

TO-220 Outline



| SYM | INCHES | | MILLIMETERS | |
|------|----------|------|-------------|-------|
| | MIN | MAX | MIN | MAX |
| A | .169 | .185 | 4.30 | 4.70 |
| A1 | .047 | .055 | 1.20 | 1.40 |
| A2 | .079 | .106 | 2.00 | 2.70 |
| b | .024 | .039 | 0.60 | 1.00 |
| b2 | .045 | .057 | 1.15 | 1.45 |
| c | .014 | .026 | 0.35 | 0.65 |
| D | .587 | .626 | 14.90 | 15.90 |
| D1 | .335 | .370 | 8.50 | 9.40 |
| (D2) | .500 | .531 | 12.70 | 13.50 |
| E | .382 | .406 | 9.70 | 10.30 |
| (E1) | .283 | .323 | 7.20 | 8.20 |
| e | .100 BSC | | 2.54 BSC | |
| e1 | .200 BSC | | 5.08 BSC | |
| H1 | .244 | .268 | 6.20 | 6.80 |
| L | .492 | .547 | 12.50 | 13.90 |
| L1 | .110 | .154 | 2.80 | 3.90 |
| ØP | .134 | .150 | 3.40 | 3.80 |
| Q | .106 | .126 | 2.70 | 3.20 |



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